Ordering number : ENN8148



SANYO Semiconductors DATA SHEET

N-Channel Silicon MOSFET

ECH8402— General-Purpose Switching Device Applications

Features

- · Low ON-resistance.
- · 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		30	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		10	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	40	Α
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm ² X0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	DataSheet4U.com Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0	30			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =30V, V _{GS} =0			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	1.0		2.4	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =5A	5.6	9.4		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =5A, V _G S=10V		11	15	mΩ
	R _{DS} (on)2	I _D =2.5A, V _G S=4V		23	32	mΩ
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		1400		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		270		pF
Reverse Transfer Capacitance	Crss	V _{DS} =10V, f=1MHz		190		pF
Turn-ON Delay Time	td(on)	See specified Test Circuit.		17		ns
Rise Time	t _r	See specified Test Circuit.		82		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit.		96		ns
Fall Time	tf	See specified Test Circuit.		53		ns

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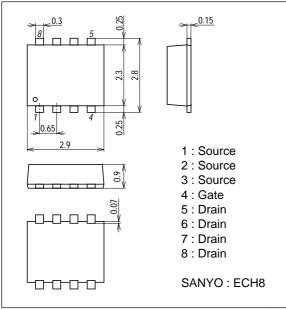
ECH8402

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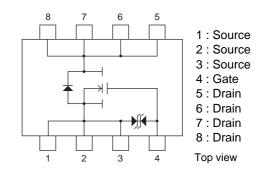
Parameter	Symbol	Conditions	Ratings			Unit
	Symbol		min	typ	max	O IIII
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =10V, I _D =5A		28		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =10V, I _D =5A		4.8		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =10V, I _D =5A		7.3		nC
Diode Forward Voltage	VSD	IS=10A, VGS=0		0.81	1.2	V

Package Dimensions

unit : mm 2222A



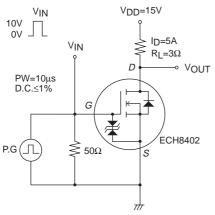
Electrical Connection

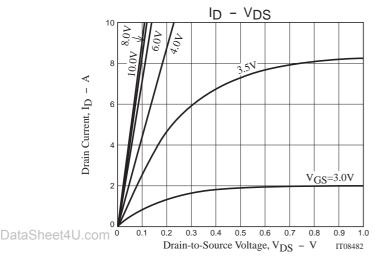


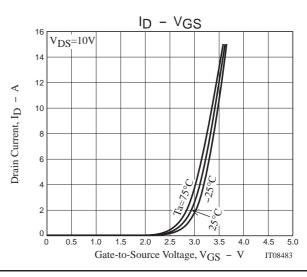
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Switching Time Test Circuit



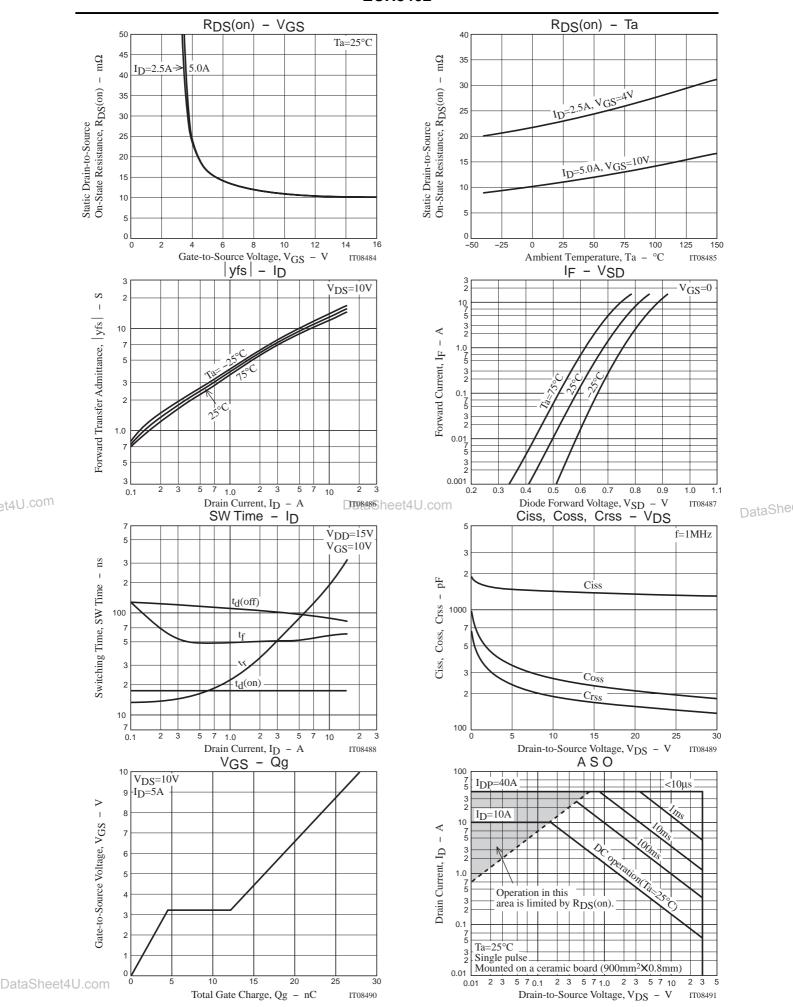




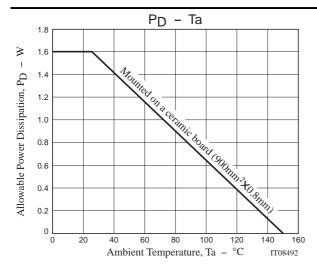
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Note on usage: Since the ECH8402 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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